

# FS50KMJ-06F

HIGH-SPEED SWITCHING USE

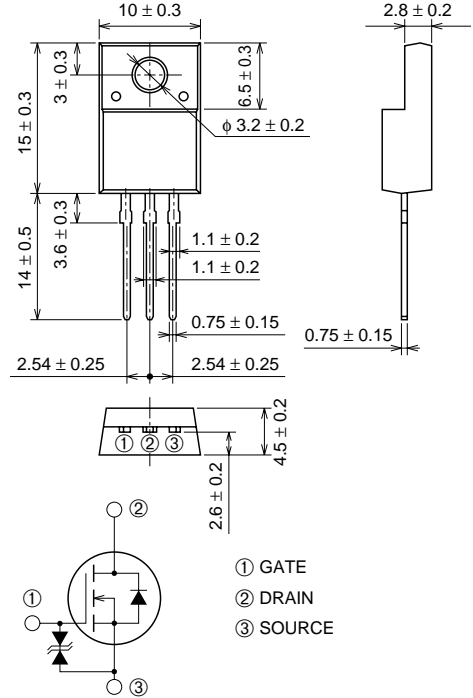
## FS50KMJ-06F



- 4V DRIVE
- V<sub>DSS</sub> ..... 60V
- r<sub>DS (ON)</sub> (MAX) ..... 14mΩ
- I<sub>D</sub> ..... 50A
- Integrated Fast Recovery Diode (TYP.) ..... 50ns

## OUTLINE DRAWING

Dimensions in mm



TO-220FN

## APPLICATION

Motor control, Lamp control, Solenoid control  
DC-DC converter, etc.

## MAXIMUM RATINGS (T<sub>c</sub> = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	60	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±20	V
I <sub>D</sub>	Drain current		50	A
I <sub>DM</sub>	Drain current (Pulsed)		200	A
I <sub>DA</sub>	Avalanche current (Pulsed)	L = 10μH	50	A
I <sub>S</sub>	Source current		50	A
I <sub>SM</sub>	Source current (Pulsed)		200	A
P <sub>D</sub>	Maximum power dissipation		30	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
V <sub>iso</sub>	Isolation voltage	AC for 1 minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	60	—	—	V
V (BR) GSS	Gate-source breakdown voltage	IG = ±100μA, VDS = 0V	±20	—	—	V
IDSS	Drain-source leakage current	VDS = 60V, VGS = 0V	—	—	100	μA
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±10	μA
VGS (th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS (ON)	Drain-source on-state resistance	ID = 25A, VGS = 10V	—	12	14	mΩ
rDS (ON)	Drain-source on-state resistance	ID = 25A, VGS = 4V	—	14	18	mΩ
VDS (ON)	Drain-source on-state voltage	ID = 25A, VGS = 10V	—	0.30	0.35	V
yfs	Forward transfer admittance	ID = 25A, VDS = 10V	—	60	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	3850	—	pF
Coss	Output capacitance		—	580	—	pF
Crss	Reverse transfer capacitance		—	320	—	pF
td (on)	Turn-on delay time	VDD = 30V, ID = 25A, VGS = 10V, RGEN = RGS = 50Ω	—	19	—	ns
tr	Rise time		—	80	—	ns
td (off)	Turn-off delay time		—	360	—	ns
tf	Fall time		—	160	—	ns
VSD	Source-drain voltage	IS = 25A, VGS = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	4.17	°C/W
trr	Reverse recovery time	IS = 50A, dis/dt = -100A/μs	—	50	—	ns